

HCS900FH120D3C1

1200V/900A Half Bridge SiC MOSFET Module

Description

The HCS900FH120D3C1 is a Half Bridge SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Motor drives and Renewable energy



Features

- Blocking voltage 1200V
- $R_{DS(on)} = 2.0 \text{ m}\Omega$
- Low thermal resistance with Si_3N_4 AMB
- 175°C maximum junction temperature
- Thermistor inside
- Low Switching Losses

Applications

- xEV Applications
- Motor Drives
- Vehicle Fast Chargers
- Smart - Grid/Grid-Tied Distributed Generation

Circuit diagram

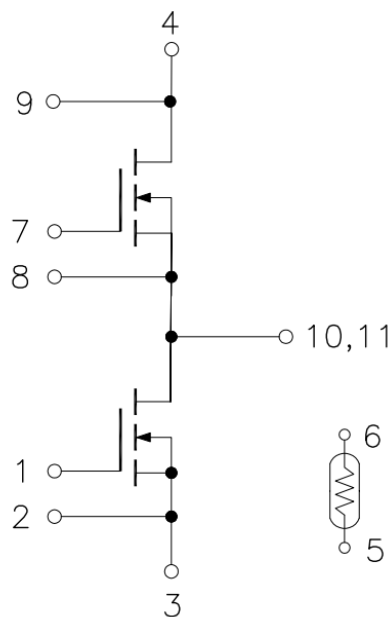


Figure1. Out drawing & circuit diagram for HCS900FH120D3C1

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Pin Configuration and Marking Information

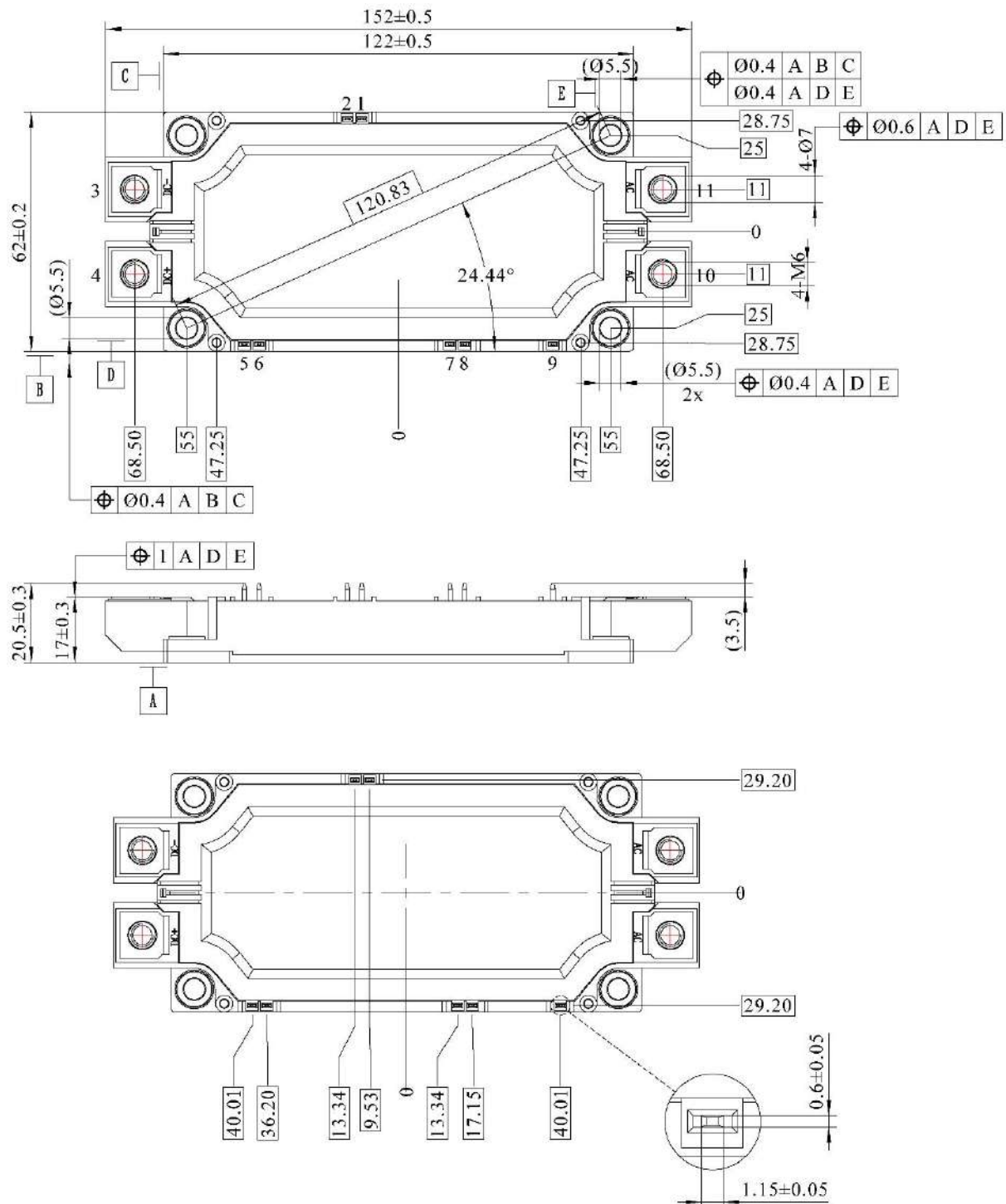


Figure 2. Pin configuration

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Module

Parameter	Condition	Value	Unit
Isolation Voltage	RMS, f =50Hz, t =1min	3.4	kV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 13	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	>400	-
Module lead resistance, terminals–chip	T _C =25°C	0.5	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	340	g

Maximum Ratings (T_j =25°C unless otherwise specified)

Symbol	Parameter	Condition	Ratings	Unit
V _{DSS}	Drain-Source Voltage	G-S Short	1200	V
V _{GSS}	Gate-Source Voltage	D-S Short, AC frequency ≥1Hz, Note1	-10 to 22	V
I _{DS}	DC Continuous Drain Current	T _C =25°C, V _{GS} =18V	1000	A
I _{DS}	DC Continuous Drain Current	T _C =60°C, V _{GS} =18V	900	A
I _{SD}	Source (Body diode) Current	T _C =25°C, with ON signal	1000	A
I _{SD}	Source (Body diode) Current	T _C =60°C, with ON signal	900	A
I _{DSM}	Pulse Forward Current	T _C =25°C, Pulse width =1ms, V _{GS} =20V, Note2	1800	A
P _{tot}	Total Power Dissipation	T _C =25°C	3000	W
T _{jmax}	Max Junction Temperature	-	175	°C
T _{stg}	Storage Temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, +18V/-5V, +18V/-4V, +15V/-4V

Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R ₂₅	Resistance	T _C =25°C	-	5	-	kΩ
R/R	Deviation of R ₁₀₀	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-value	R ₂ =R ₂₅ exp [B _{25/50} (1/T ₂ - 1/(298,15 K))]	-	3375	-	K
B _{25/80}	B-value	R ₂ =R ₂₅ exp [B _{25/80} (1/T ₂ - 1/(298,15 K))]	-	3411	-	K
B _{25/100}	B-value	R ₂ =R ₂₅ exp [B _{25/100} (1/T ₂ - 1/(298,15 K))]	-	3433	-	K

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MOSFET Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =900μA		1200	-	-	V
I _{DSS}	Zero gate voltage drain Current	V _{DS} =1200V, V _{GS} =0V		-	30	-	μA
V _{GS(th)}	Gate-source threshold Voltage	I _D =315mA	T _j =25°C	1.8	2.7	-	V
		V _{DS} =V _{GS}	T _j =175°C	-	2.1	-	V
I _{GSS}	Gate-Source Leakage Current	V _{GS} =20V, V _{DS} =0V, T _j =25°C		-	-	900	nA
R _{DS(on)} (Chip)	Static drain-source	I _D =900A	T _j =25°C	-	2.5	3.3	mΩ
		V _{GS} =+15V	T _j =175°C	-	3.5	-	mΩ
	On-state resistance	I _D =900A	T _j =25°C	-	2.0	-	mΩ
		V _{GS} =+18V	T _j =175°C	-	2.8	-	mΩ
V _{DS(on)} (Chip)	Static drain-source	I _D =900A	T _j =25°C	-	2.25	2.97	V
		V _{GS} =+15V	T _j =175°C	-	3.15	-	V
	On-state Voltage	I _D =900A	T _j =25°C	-	1.80	-	V
		V _{GS} =+18V	T _j =175°C	-	2.52	-	V
C _{iss}	Input Capacitance	V _D =1000V, V _{GS} =0V f =200kHz, V _{AC} =25mV		-	52.2	-	nF
C _{oss}	Output Capacitance			-	1.60	-	nF
C _{rss}	Reverse transfer Capacitance			-	0.13	-	nF
R _{Gint}	Internal gate resistor	-		-	0.7	-	Ω
Q _G	Total gate charge	V _{DD} =800V, I _D =540A, V _{GS} =+18/- 5V		-	1890	-	nC
t _{d(on)}	Turn-on delay time	V _{DD} =600V I _D =900A V _{GS} =+18/-4V R _{gon} /R _{goff} =3.3/2.2Ω Inductive load switching operation	T _j =25°C	-	51	-	ns
			T _j =150°C	-	47	-	
t _r	Rise time		T _j =25°C	-	29	-	ns
			T _j =150°C	-	27	-	
t _{d(off)}	Turn-off delay time		T _j =25°C	-	116	-	ns
			T _j =150°C	-	132	-	
t _f	Fall time		T _j =25°C	-	25	-	ns
			T _j =150°C	-	42	-	
E _{on}	Turn-on power dissipation		T _j =25°C	-	35.5	-	mJ
			T _j =150°C	-	41.7	-	
E _{off}	Turn-off power dissipation		T _j =25°C	-	18.5	-	mJ
			T _j =150°C	-	21.8	-	
R _{th(j-c)}	FET Thermal Resistance	Junction to Case		-	0.05	-	K/W
R _{th(c-f)}	Contact thermal Resistance	With thermal conductive grease, Note3		-	0.015	-	K/W

Note3: Assumes Thermal Conductivity of grease is 0.9W/m · K and thickness is 50um.

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Body Diode Electrical characteristics (T_j=25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V _{SD}	Body Diode Forward Voltage	V _{GS} =-5V I _{SD} =900A	T _j =25°C	-	6.3	-	V
			T _j =175°C	-	5.6	-	
T _{rr}	Reverse recovery time	V _{DD} =600V I _D =900A	T _j =25°C	-	29	-	ns
			T _j =150°C	-	47	-	
Q _{rr}	Reverse recovery charge	V _{GS} =+18/-4V R _{gon} /R _{goff} =3.3/2.2Ω	T _j =25°C	-	3.5	-	uC
			T _j =150°C	-	13.2	-	
E _{rr}	Diode switching power dissipation	Inductive load switching operation	T _j =25°C	-	1.82	-	mJ
			T _j =150°C	-	5.65	-	

Test Conditions

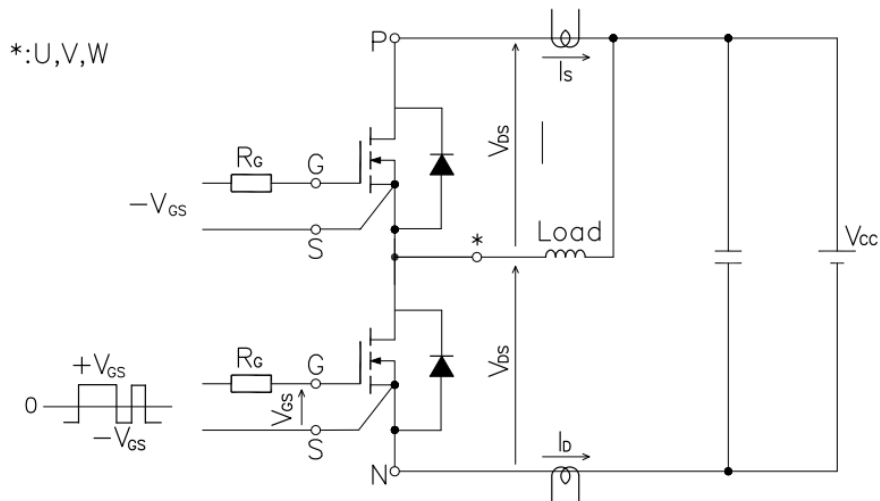


Figure 3. Switching time measure circuit

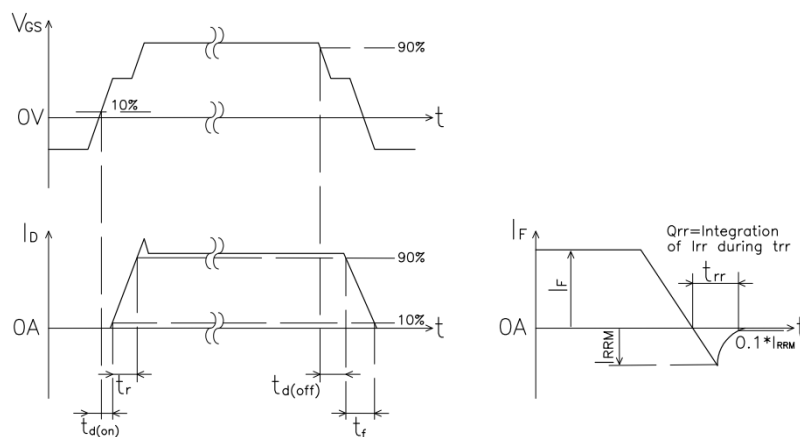


Figure 4. Switching time definition

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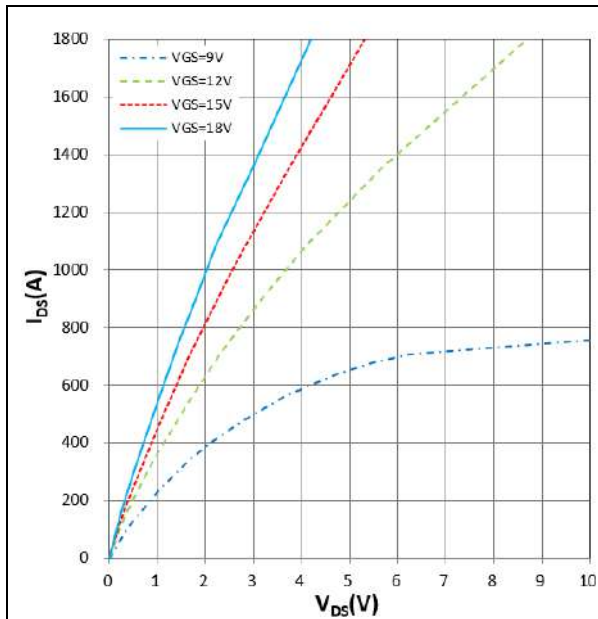


Figure 5. I_{DS} vs V_{DS}
 $T_j = 25^\circ\text{C}$, V_{GS} parameter

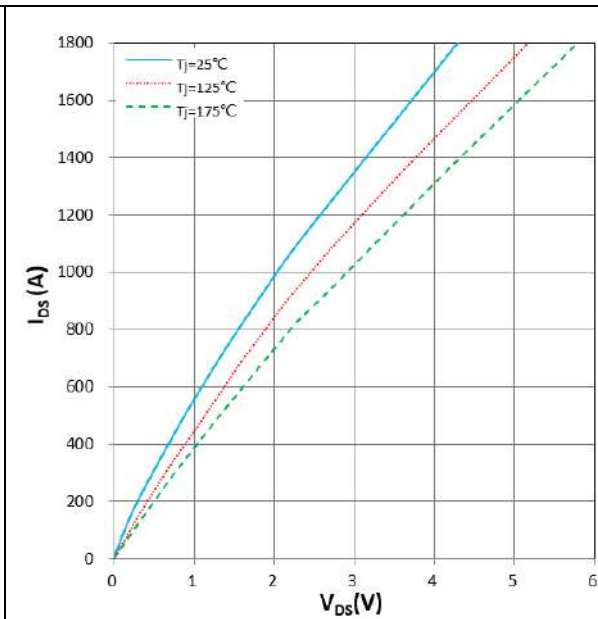


Figure 6. I_{DS} vs V_{DS}
 $V_{GS} = 18\text{V}$, T_j parameter

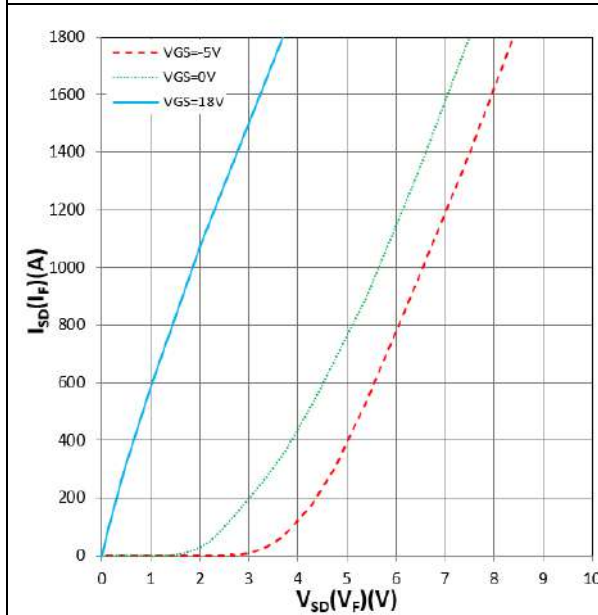


Figure 7. $I_{SD}(I_F)$ vs $V_{SD}(V_F)$
 $T_j = 25^\circ\text{C}$, V_{GS} parameter

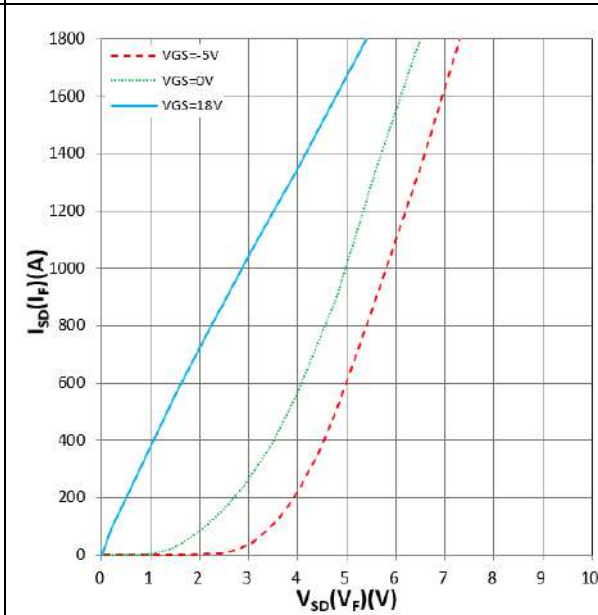


Figure 8. $I_{SD}(I_F)$ vs $V_{SD}(V_F)$
 $T_j = 175^\circ\text{C}$, V_{GS} parameter

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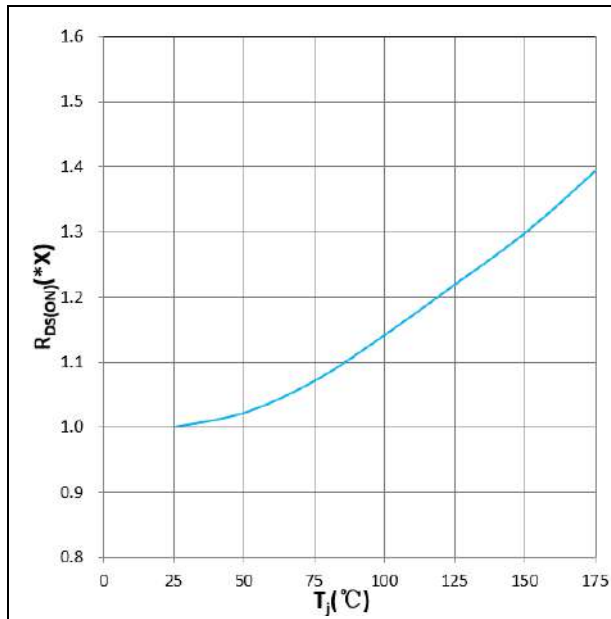


Figure 9. $R_{DS(ON)}$ vs T_J
 $V_{GS}=+18V$, $I_D=900A$, $1.0X=2.0m\Omega$

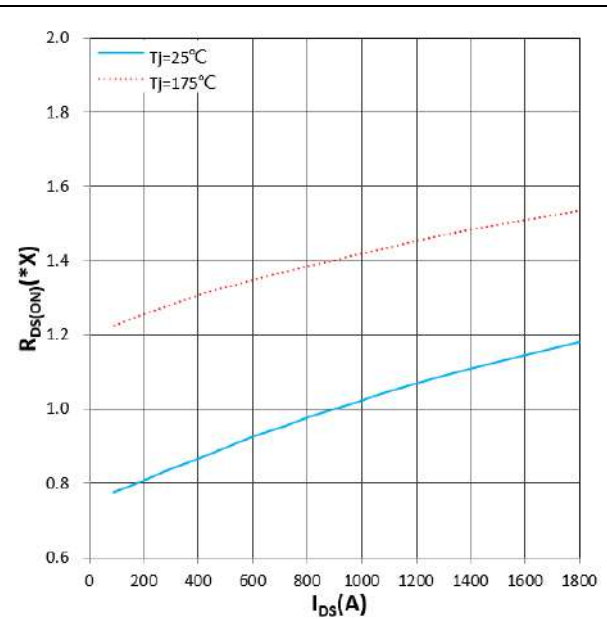


Figure 10. $R_{DS(ON)}$ vs I_{DS}
 $T_J=25^\circ C/175^\circ C$, $V_{GS}=+18V$, $1.0X=2.0m\Omega$

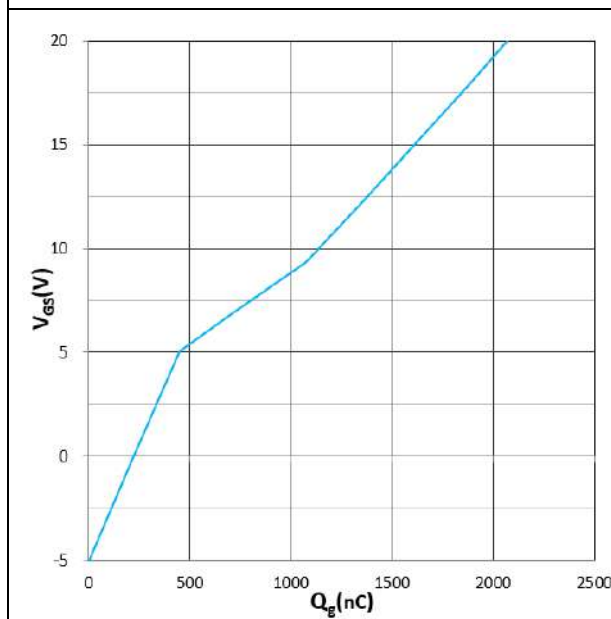


Figure 11. V_{GS} vs Q_g
 $T_J=25^\circ C$, $V_{DS}=800V$, $I_D=540A$

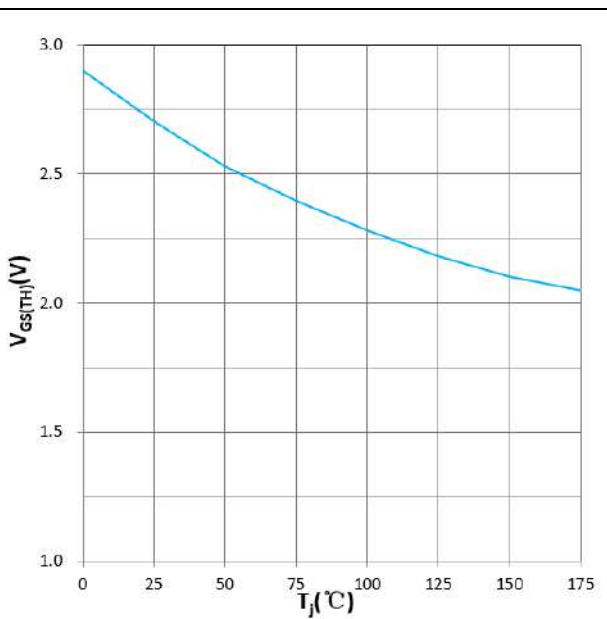


Figure 12. $V_{GS(TH)}$ vs T_J
 $V_{GS}=V_{DS}$, $I_D=315mA$

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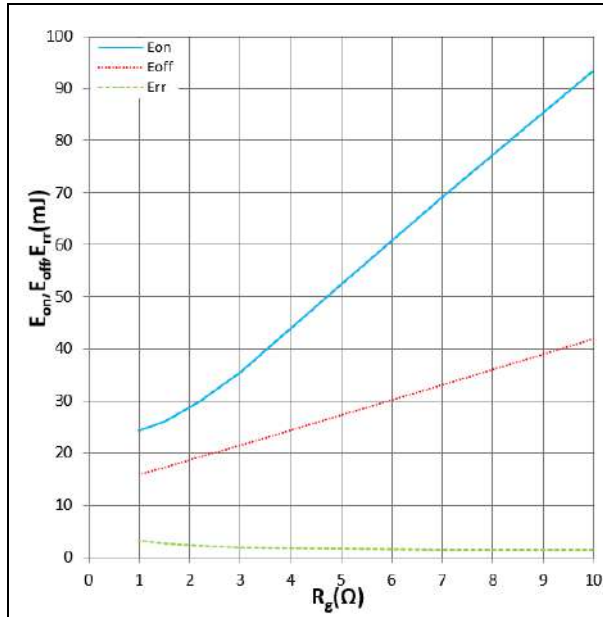


Figure 13. E_{on} , E_{off} , E_{rr} vs R_g
 $T_j = 25^\circ\text{C}$, $V_{DD} = 600\text{V}$, $V_{GS} = +18\text{V}/-4\text{V}$, $I_D = 900\text{A}$
Inductive Load

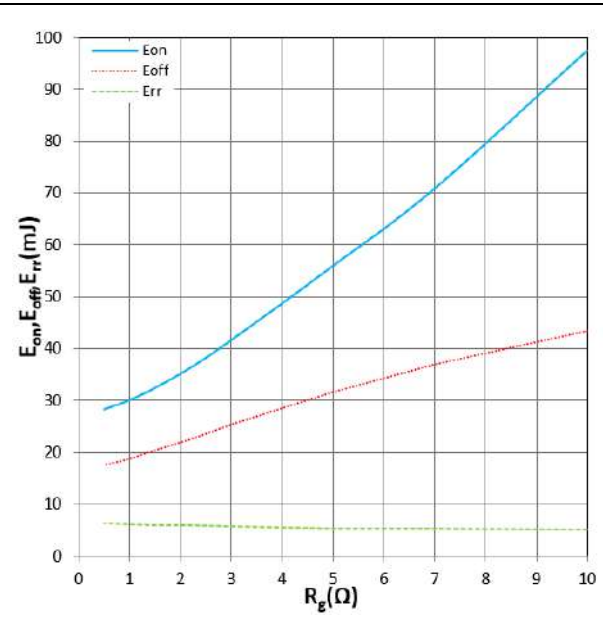


Figure 14. E_{on} , E_{off} , E_{rr} vs R_g
 $T_j = 150^\circ\text{C}$, $V_{DD} = 600\text{V}$, $V_{GS} = +18\text{V}/-4\text{V}$, $I_D = 900\text{A}$
Inductive Load

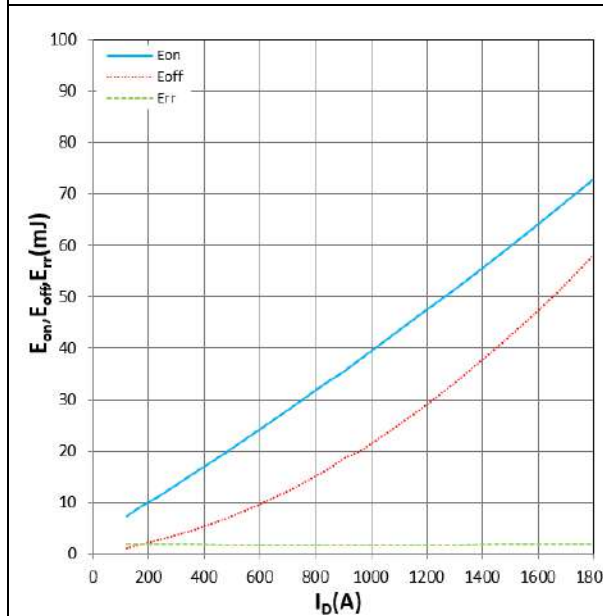


Figure 15. E_{on} , E_{off} , E_{rr} vs I_D
 $T_j = 25^\circ\text{C}$, $V_{DD} = 600\text{V}$, $V_{GS} = +18\text{V}/-4\text{V}$,
 $R_{gon}/R_{goff} = 3.3/2.2\Omega$, Inductive Load

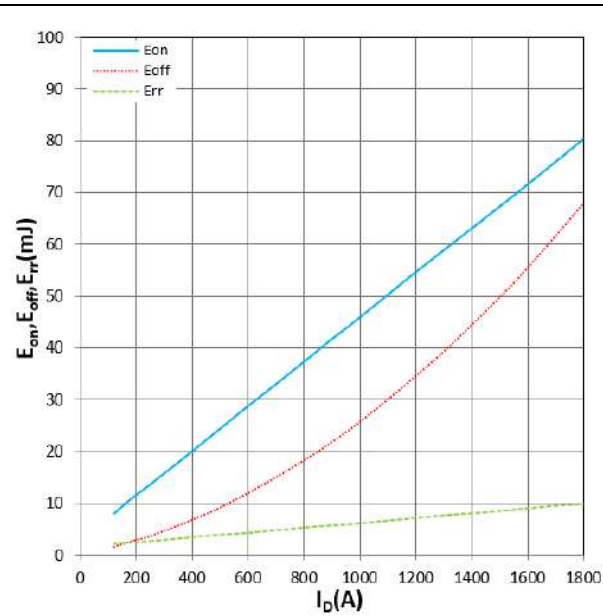


Figure 16. E_{on} , E_{off} , E_{rr} vs I_D
 $T_j = 150^\circ\text{C}$, $V_{DD} = 600\text{V}$, $V_{GS} = +18\text{V}/-4\text{V}$,
 $R_{gon}/R_{goff} = 3.3/2.2\Omega$, Inductive Load

HCS900FH120D3C1**1200V/900A Half Bridge SiC MOSFET Module****IMPORTANT NOTICE:**

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Revision History

Document Version	Description of Changes
RevX.0.1	Released

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